

ABSTRACT OF THE DISCLOSURE

A resonant-cavity light-emitting diode includes a semiconductor light-emitting layer sandwiched between an under and an upper semiconductor distributed Bragg reflector mirror layer, which are formed on the substrate, a light extracting section formed on the upper semiconductor distributed Bragg reflector mirror layer and having an opening to extract light from the semiconductor light-emitting layer, and a groove formed by removing portions of the semiconductor light-emitting layer, under and upper semiconductor distributed Bragg reflector mirror layers which lie in a peripheral portion of the opening of the light extraction section and reach the under semiconductor distributed Bragg reflector mirror layer, the inner wall of the groove being formed to reflect part of light emitted from the semiconductor light-emitting layer into the groove.